

**20V P-Channel MOSFET**

**Features**

- Surface Mount Package
- P-Channel Switch with Low  $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected

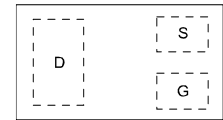
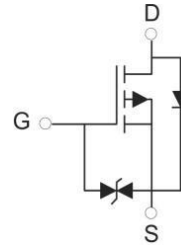
**Application**

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

**MOSFET Product Summary**

$V_{bss}$	$R_{DS(ON) Max}$	$I_D$
-20V	1.2Ω @ $V_{GS}=-4.5V$	-0.66A
	1.5Ω @ $V_{GS}=-2.5V$	

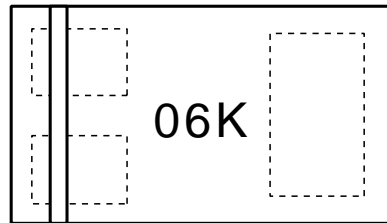
**Package and Pin Configuration**



Circuit diagram

DFN1006-3L

**Marking Information**



06K = Device Marking Code

**Absolute Maximum Ratings ( $T_A=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	±10	V
Continuous Drain Current	$I_D$	-0.66	A
Pulsed Drain Current	$I_{DM}$	-1.2	A
Power Dissipation	$P_D$	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~ +150	°C

**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

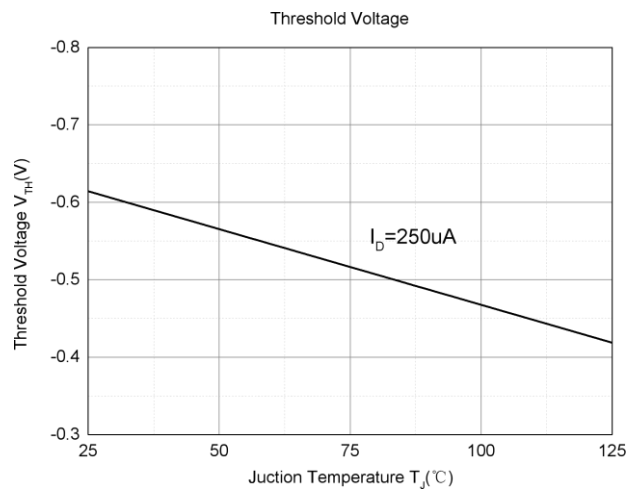
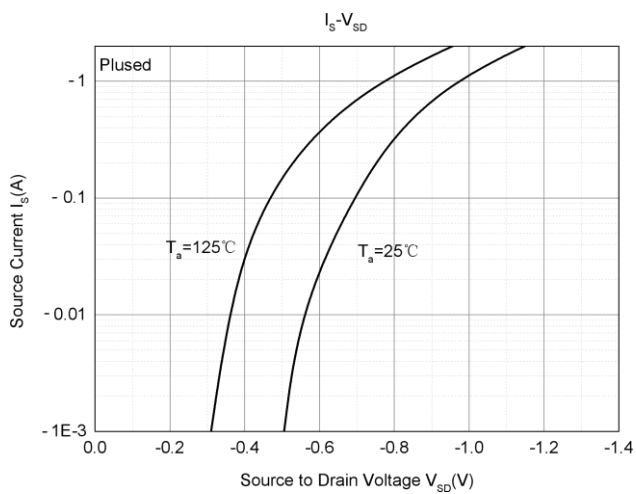
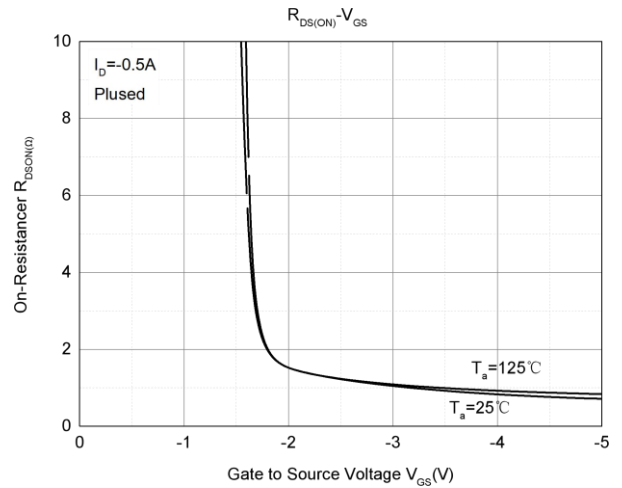
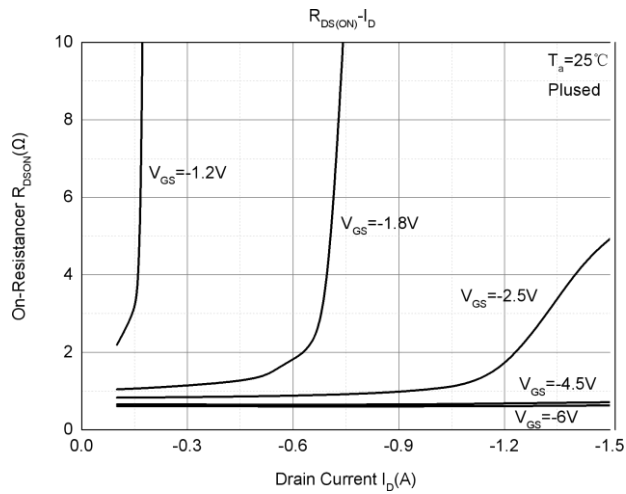
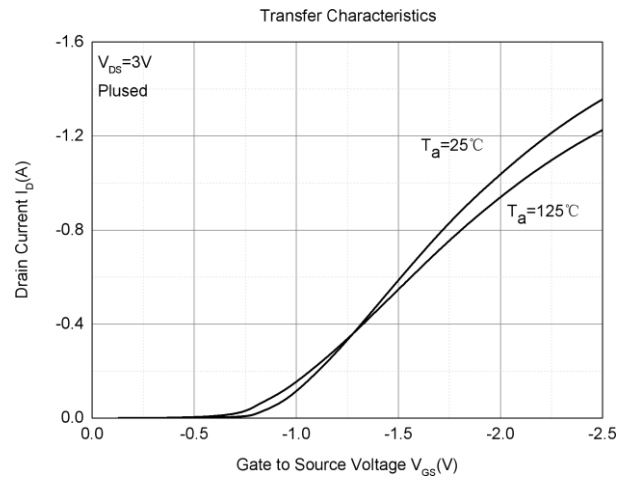
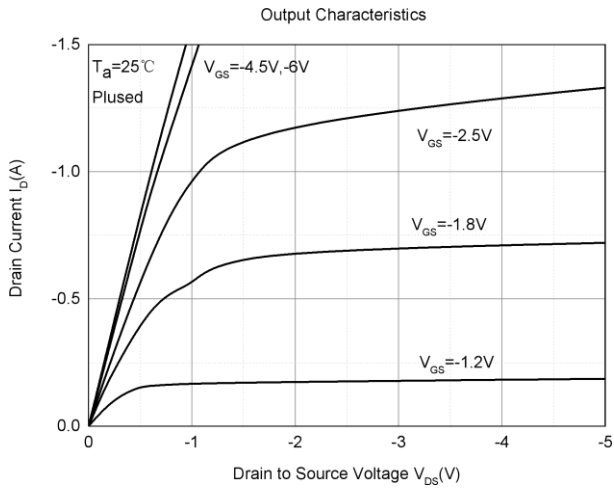
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -16V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 8V, V_{DS} = 0V$			$\pm 10$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.3	-0.65	-1	V
Drain-source on-resistance <sup>1)</sup>	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -0.5A$			1.2	$\Omega$
		$V_{GS} = -2.5V, I_D = -0.2A$			1.5	
		$V_{GS} = -1.8V, I_D = -0.1A$			2.2	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113		$\mu F$
Output Capacitance	$C_{oss}$			15		
Reverse Transfer Capacitance	$C_{rss}$			9		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -10V, I_D = -200mA,$ $V_{GS} = -4.5V, R_G = 10\Omega$		9		ns
Turn-on rise time	$t_r$			5.7		
Turn-off delay time	$t_{d(off)}$			32.6		
Turn-off fall time	$t_f$			20.3		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$V_{SD}$	$V_{GS} = 0V, I_S = -0.5 A$			-1.2	V

Notes:

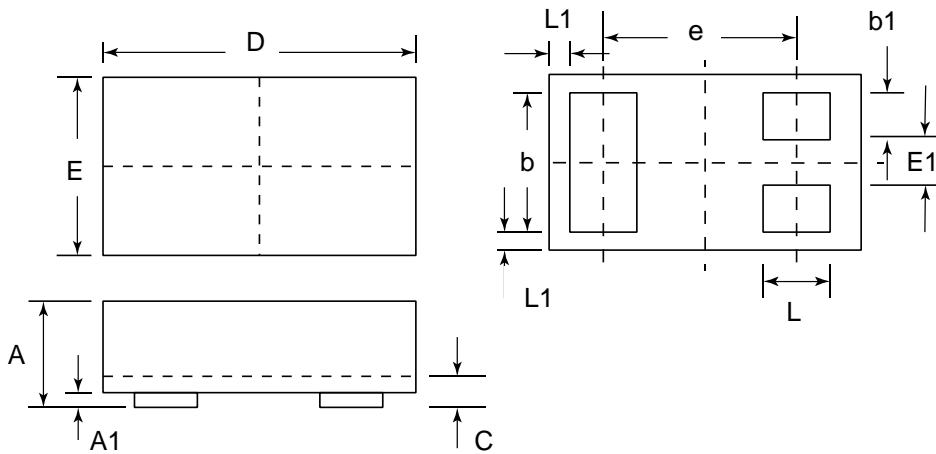
1) Pulse Test: Pulse Width < 300 $\mu s$ , Duty Cycle  $\leq 2\%$ .

2) Guaranteed by design, not subject to production testing.

**Typical Characteristics**

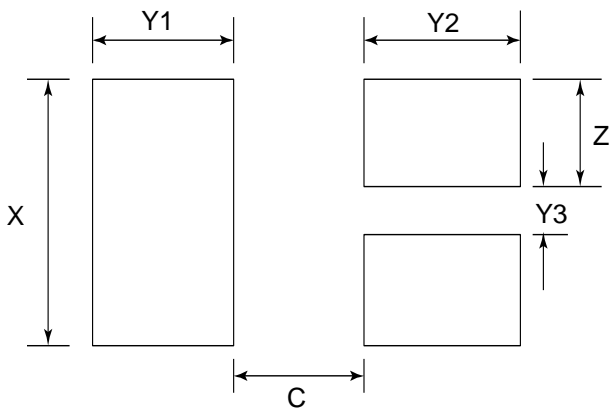


**DFN1006-3L Package Outline Drawing**



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
C	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

**Suggested Land Pattern**



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008